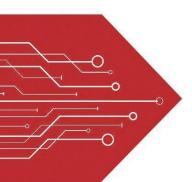
MSKSEMI















ESD

TVS

TSS

MOV

GDT

PLED

Broduct data sheet



FEATURES

- ◆ Glass passivated device
- ◆ Ideal for surface mouted applications
- ◆ Low reverse leakage
- ◆ Metallurgically bonded construction
- ◆ High temperature soldering guaranteed: 250°C/10 seconds,0.375"(9.5mm) lead length, 5 lbs. (2.3kg) tension

MECHANICAL DATA

Case: JEDEC SOD-123FL molded plastic body over passivated chip

Terminals: Solderable per MIL-STD-750,

Method 2026

Polarity: Color band denotes cathode end

Mounting Position: Any Weight: 0.0007 ounce, 0.02 grams

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Ratings at 25°C ambient temperature unless otherwise specified. Single phase half-wave 60Hz, resistive or inductive load, for capacitive load current derate by 20%.

	P/N	SOD4001 -MS	SOD4002 -MS	SOD4003 -MS	SOD4004 -MS	SOD4005 -MS	SOD4006 -MS	SOD4007 -MS	UNITS
	MARK	A1	A2	A3	A4	A5	A6	A7	
Maximum repetitive peak reverse voltage	VRRM	50	100	200	400	600	800	1000	VOLTS
Maximum RMS voltage	VRMS	35	70	140	280	420	560	700	VOLTS
Maximum DC blocking voltage	VDC	50	100	200	400	600	800	1000	VOLTS
Maximum average forward rectified current at Ta=65°C (NOTE 1)	l(AV)	1.0					Amp		
Peak forward surge current 8.3ms single half sine-wave superimposed on rated load (JEDEC Method) TL=25°C	IFSM	25.0					Amps		
Maximum instantaneous forward voltage at 1.0A	VF	1.0			Volts				
Maximum DC reverse current Ta=25°C at rated DC blocking voltage Ta=125°C	I _R	10.0 50.0				μА			
Typical junction capacitance (NOTE 2)	Cı	4			pF				
Typical thermal resistance (NOTE 3)	Rθja	180			K/W				
Operating junction and storage temperature range	ТЈ,Тѕтс	-55 to +150				C			

Note: 1. Averaged over any 20ms period.

2. Measured at 1MHz and applied reverse voltage of 4.0V D.C.

3. Thermal resistance from junction to ambient at 0.375" (9.5mm)lead length, P.C.B. mounted



INSTANTANEOUS REVERSECURRENT

 μ AMPERES

CAPACITANCE, pF

FIG.1 -TYPICALFORWARDCHARACTERISTIC

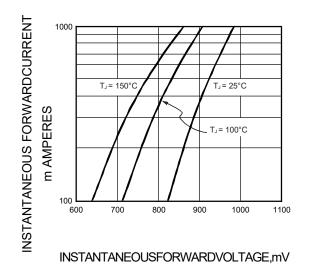
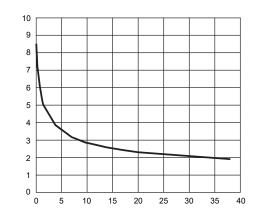
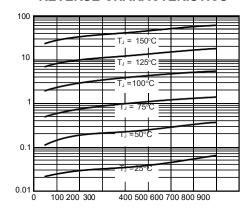


FIG.2 -- TYPICALJUNCTIONCAPACITANCE



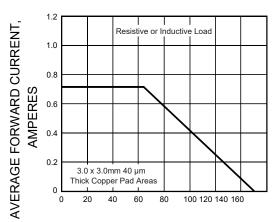
REVERSEVOLTAGE, VOLTS

FIG.3 --TYPICAL INSTANTANEOUS REVERSE CHARACTERISTICS



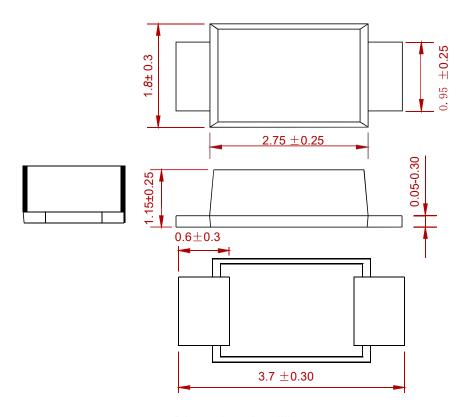
INSTANTANEOUS REVERSE VOLTAGE, V

FIG.4 -- FORWARDDERATINGCURVE



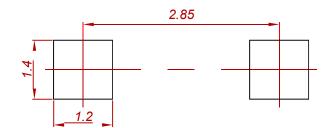
AMBIENT TEMPERATOR

PACKAGE MECHANICAL DATA



Dimensions in millimeters

Suggested Pad Layout



Note:

- 1. Controlling dimension: in millimeters.
- 2.General tolerance:± 0.05mm.
- 3. The pad layout is for reference purposes only.

REEL SPECIFICATION

P/N	PKG	QTY
SOD4001-MS THRU SOD4007-MS	SOD-123FL	3000



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